2SK3948

Silicon N-channel junction FET

For impedance conversion in low frequency For electret capacitor microphone

■ Features

- Low noise voltage NV
- High voltage gain GV
- Thin package: TSSSMini3-F1 (1.2 mm × 1.2 mm × 0.33 mm)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source voltage (Gate open)	$V_{\rm DSO}$	20	V	
Drain-gate voltage (Souece open)	V_{DGO}	20	V	
Drain-source current (Gate open)	I_{DSO}	2	mA	
Drain-gate current (Souece open)	I_{DGO}	2	mA	
Power dissipation	P _D	100	mW	
Operating ambient temperature	Topr	-20 to +80	°C	
Storage temperature	T _{stg}	-55 to +125	°C	

Package

Code

TSSSMini3-F1

- Pin Name
 - 1: Drain
 - 2: Source
 - 3: Gate
- Marking Symbol: 4X

■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

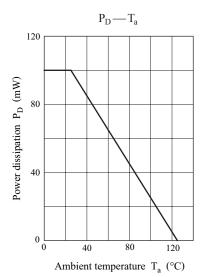
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain current *1	I_{D}	$V_{DD} = 2.0 \text{ V}, R_d = 2.2 \text{ k}\Omega \pm 1\%$	170	(0)	470	μA
Drain-source current *2	$I_{ m DSS}$	$V_{DD} = 2.0 \text{ V}, R_d = 2.2 \text{ k}\Omega \pm 1\%, V_{GS} = 0$	180	0 00	450	μΑ
Mutual conductance	g _m	$V_{DS} = 2.0 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	660	1500		μS
Noise voltage *3	NV	V_{DD} = 2.0 V, R_d = 2.2 k Ω ± 1% C_O = 5 pF, A-curve			8	μV
Voltage gain	G_{V1}	$V_{DD} = 2.0 \text{ V}, R_d = 2.2 \text{ k}\Omega \pm 1\%$ $C_O = 5 \text{ pF}, e_G = 10 \text{ mV}, f = 1 \text{ kHz}$	-5.0	-1.0		
	G_{V2}	$V_{DD} = 12 \text{ V}, R_d = 2.2 \text{ k}\Omega \pm 1\%$ $C_O = 5 \text{ pF}, e_G = 10 \text{ mV}, f = 1 \text{ kHz}$	-3.0	3.0		
	G_{V3}	$V_{DD} = 1.5 \text{ V}, R_d = 2.2 \text{ k}\Omega \pm 1\%$ $C_O = 5 \text{ pF}, e_G = 10 \text{ mV}, f = 1 \text{ kHz}$	-7.0	-1.5		dB
Voltage gain difference	$\Delta G_{V}.f ^{*4}$	$V_{DD} = 2.0 \text{ V}, R_d = 2.2 \text{ k}\Omega \pm 1\%$ $C_O = 5 \text{ pF}, e_G = 10 \text{ mV}$ $f = 1 \text{ kHz to } 70 \text{ Hz}$		0.0	1.7	
	$ G_{V1}-G_{V3} $			0.5	1.0	dB

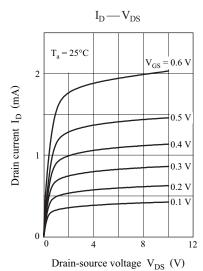
- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
 - 2. A protection diode is built-in between gate and source of transistor. However if forward current flows between gate and source transistor might be damaged. So please be careful not insert reverse.
 - 3. *1: I_D is assured for I_{DSS} .
 - *2: Rank classification

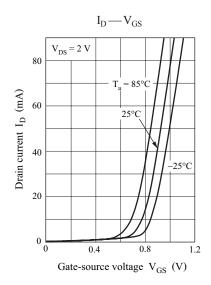
Rank	Т	U
$I_{D}(\mu A)$	170 to 330	270 to 470
$I_{DSS}(\mu A)$	180 to 320	280 to 450

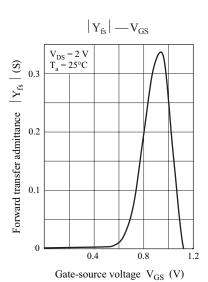
- *3: NV is assured for design.
- *4: $\Delta |G_V|$. f| is assured for AQL 0.065. (The measurement method is used by source-grounded circuit.)

2SK3948 Panasonic





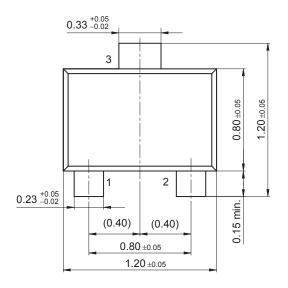


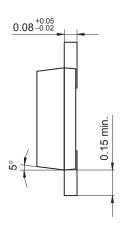


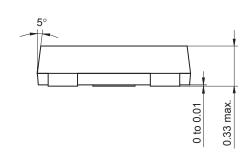
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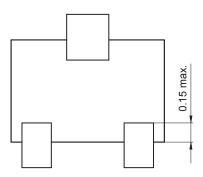
TSSSMini3-F1

Unit: mm









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